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Diodes Incorporated DMG8880LK3-13

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Datasheet of DMG8880LK3-13 - MOSFET N-CH 30V 11A TO252-3L

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DMG8880LK3

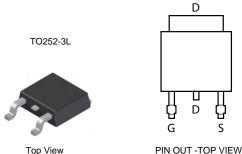
#### N-CHANNEL ENHANCEMENT MODE MOSFET

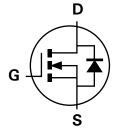
#### **Features**

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

- Case: TO252-3L
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Weight: 0.33 grams (approximate)





**Equivalent Circuit** 

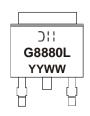
## Ordering Information (Note 3)

| Part Number   | Case     | Packaging          |
|---------------|----------|--------------------|
| DMG8880LK3-13 | TO252-3L | 2500 / Tape & Reel |

Notes:

- 1. No purposefully added lead.
- Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com.
  For packaging details, go to our website at http://www.diodes.com.

## **Marking Information**



G8880L = Product Type Marking Code )!! = Manufacturer's Marking YYWW = Date Code Marking YY = Year (ex: 09 = 2009) WW = Week (01 ~ 53)

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DMG8880LK3

## Maximum Ratings @TA = 25°C unless otherwise specified

| Characteristic  |                  |  | Symbol           | Value      | Unit |
|---|------------------|--|------------------|------------|------|
| Drain-Source Voltage                                    | V <sub>DSS</sub> | 30   | V                |            |      |
| Gate-Source Voltage                                     |                  |  | V <sub>GSS</sub> | ±20        | V    |
| Continuous Drain Current (Note 4) V <sub>GS</sub> = 10V | Steady<br>State  | T <sub>A</sub> = 25°C<br>T <sub>A</sub> = 85°C | I <sub>D</sub>   | 11<br>8    | А    |
| Continuous Drain Current (Note 5) V <sub>GS</sub> = 10V | Steady<br>State  | T <sub>A</sub> = 25°C<br>T <sub>A</sub> = 85°C | I <sub>D</sub>   | 16.5<br>12 | А    |
| Pulsed Drain Current (Note 6)                           | I <sub>DM</sub>  | 48   | Α                |            |      |

## **Thermal Characteristics**

| Characteristic  | Symbol                            | Value       | Unit |
|---|-----------------------------------|-------------|------|
| Power Dissipation (Note 4)  | P <sub>D</sub>                    | 1.68        | W    |
| Thermal Resistance, Junction to Ambient @T <sub>A</sub> = 25°C (Note 4) | $R_{\theta JA}$                   | 74.3        | °C/W |
| Power Dissipation (Note 5)  | P <sub>D</sub>                    | 4.1         | W    |
| Thermal Resistance, Junction to Ambient @T <sub>A</sub> = 25°C (Note 5) | R <sub>0JA</sub>                  | 30.8        | °C/W |
| Operating and Storage Temperature Range                                 | T <sub>J</sub> , T <sub>STG</sub> | -55 to +150 | °C   |

## Electrical Characteristics @TA = 25°C unless otherwise specified

| Characteristic  | Symbol               | Min | Тур    | Max       | Unit               | Test Condition  |  |
|---|----------------------|-----|--------|-----------|--------------------|---|--|
| OFF CHARACTERISTICS (Note 7)                          | Cymbol               |     | ıур    | IVIGA     | Oilit              | rest condition  |  |
| Drain-Source Breakdown Voltage                        | BV <sub>DSS</sub>    | 30  | -      | -         | V                  | $V_{GS} = 0V, I_D = 250\mu A$   |  |
| Zero Gate Voltage Drain Current T <sub>J</sub> = 25°C | I <sub>DSS</sub>     | -   | -      | 1.0       | μΑ                 | V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V   |  |
| Gate-Source Leakage                                   | I <sub>GSS</sub>     | -   | -      | ±100      | nA                 | $V_{GS} = \pm 20V, V_{DS} = 0V$   |  |
| ON CHARACTERISTICS (Note 7)                           |                      |     |        |           |                    |   |  |
| Gate Threshold Voltage                                | V <sub>GS(th)</sub>  | 1.2 | 1.5    | 2.3       | V                  | $V_{DS} = V_{GS}, I_{D} = 250 \mu A$  |  |
| Static Drain-Source On-Resistance                     | R <sub>DS (ON)</sub> | -   | 5<br>8 | 7.5<br>12 | $\mathbf{m}\Omega$ | $V_{GS} = 10V, I_D = 11.6A$<br>$V_{GS} = 4.5V, I_D = 10.7A$                         |  |
| Forward Transfer Admittance                           | Y <sub>fs</sub>      | -   | 22     | -         | S                  | V <sub>DS</sub> = 15V, I <sub>D</sub> = 15A   |  |
| Diode Forward Voltage                                 | V <sub>SD</sub>      | -   | 0.7    | 1.0       | V                  | V <sub>GS</sub> = 0V, I <sub>SD</sub> = 2.1A  |  |
| DYNAMIC CHARACTERISTICS (Note 8)                      |                      |     | l      | L         |                    | ,   |  |
| Input Capacitance                                     | C <sub>iss</sub>     | -   | 1289   | -         | pF                 | 151/1/ 01/  |  |
| Output Capacitance                                    | Coss                 | -   | 187    | -         | pF                 | $V_{DS} = 15V, V_{GS} = 0V,$<br>-f = 1.0MHz   |  |
| Reverse Transfer Capacitance                          | C <sub>rss</sub>     | -   | 162    | -         | pF                 | 1 = 1.0WH12   |  |
| Gate Resistance                                       | Rg                   | -   | 0.97   | -         | Ω                  | $V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$  |  |
| Total Gate Charge at 10V                              | Qg                   | -   | 27.6   | -         | nC                 | V <sub>GS</sub> = 10V, V <sub>DS</sub> = 15V,<br>I <sub>D</sub> = 11.6A, Ig = 1.0mA |  |
| Total Gate Charge at 5V                               | $Q_{g}$              | -   | 14.4   | -         | nC                 |   |  |
| Gate-Source Charge                                    | $Q_{gs}$             | -   | 3.6    | -         | nC                 | $V_{GS} = 5V, V_{DS} = 15V,$  |  |
| Gate-Drain Charge                                     | $Q_gd$               | -   | 4.9    | -         | nC                 | I <sub>D</sub> = 11.6A  |  |
| Turn-On Delay Time                                    | t <sub>D(on)</sub>   | -   | 7.04   | -         | ns                 |   |  |
| Turn-On Rise Time                                     | t <sub>r</sub>       | -   | 17.52  | -         | ns                 | $V_{DD} = 15V, V_{GS} = 10V,$   |  |
| Turn-Off Delay Time                                   | t <sub>D(off)</sub>  | -   | 36.13  | -         | ns                 | $R_G = 11\Omega$ , $I_D = 11.6A$ ,<br>$R_L = 1.3\Omega$                             |  |
| Turn-Off Fall Time                                    | t <sub>f</sub>       | -   | 19.67  | -         | ns                 | UL = 1.322  |  |
| Body Diode Reverse Recovery Time                      | t <sub>rr</sub>      | -   | 17.6   | -         | ns                 | I <sub>F</sub> = 20A, dl/dt = 500A/μs   |  |
| Body Diode Reverse Recovery Charge                    | Qrr                  | -   | 65.9   | -         | nC                 | I <sub>F</sub> = 20A, dl/dt = 500A/μs   |  |

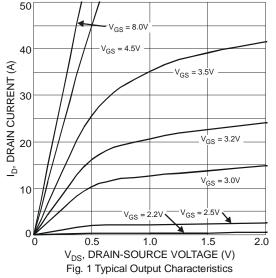
Notes:

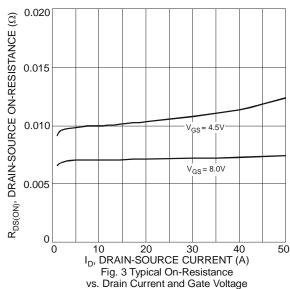
- 4. Device mounted on FR-4 PCB, with minimum recommended pad layout, single sided.
- 5. Device mounted on 2" x 2" FR-4 PCB with high coverage 2oz. copper, single sided.
- 6. Repetitive rating, pulse width limited by junction temperature and current limited by package.
- 7. Short duration pulse test used to minimize self-heating effect. 8. Guaranteed by design. Not subject to production testing.

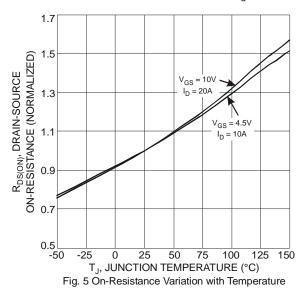
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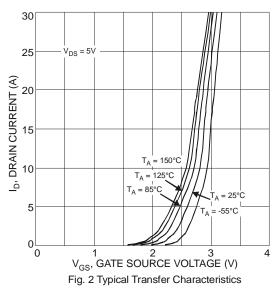
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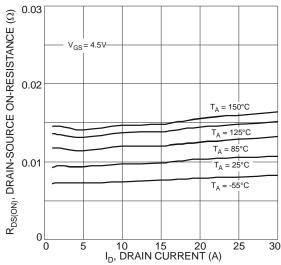


Fig. 4 Typical Drain-Source On-Resistance vs. Drain Current and Temperature

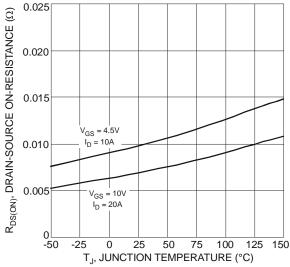


Fig. 6 On-Resistance Variation with Temperature

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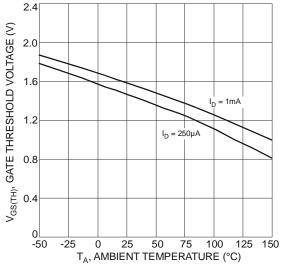
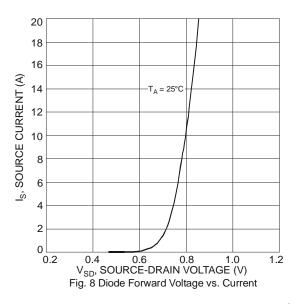
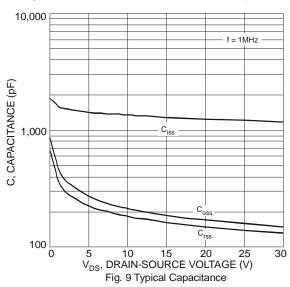
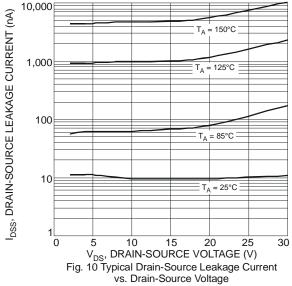
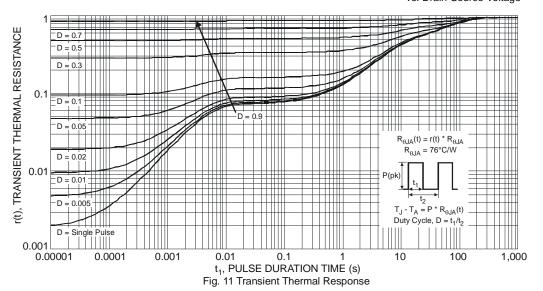


Fig. 7 Gate Threshold Variation vs. Ambient Temperature









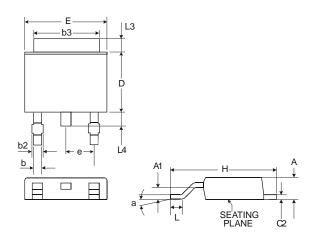
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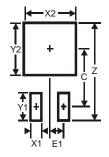
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## **Package Outline Dimensions**



| TO252-3L             |            |      |       |  |  |
|----------------------|------------|------|-------|--|--|
| Dim                  | Min        | Тур  | Max   |  |  |
| Α                    | 2.19       | 2.29 | 2.39  |  |  |
| A1                   | 0.97       | 1.07 | 1.17  |  |  |
| b                    | 0.64       | 0.76 | 0.88  |  |  |
| b2                   | 0.76       | 0.95 | 1.14  |  |  |
| b3                   | 5.21       | 5.33 | 5.50  |  |  |
| C2                   | 0.45       | 0.51 | 0.58  |  |  |
| D                    | 6.00       | 6.10 | 6.20  |  |  |
| Е                    | 6.45       | 6.58 | 6.70  |  |  |
| е                    | 2.286 Typ. |      |       |  |  |
| Η                    | 9.40       | 9.91 | 10.41 |  |  |
| L                    | 1.40       | 1.59 | 1.78  |  |  |
| L3                   | 0.88       | 1.08 | 1.27  |  |  |
| L4                   | 0.64       | 0.83 | 1.02  |  |  |
| а                    | 0°         | -    | 10°   |  |  |
| All Dimensions in mm |            |      |       |  |  |

## **Suggested Pad Layout**



| Dimensions | Value (in mm) |
|------------|---------------|
| Z          | 11.6          |
| X1         | 1.5           |
| X2         | 7.0           |
| Y1         | 2.5           |
| Y2         | 7.0           |
| С          | 6.9           |
| F1         | 2.3           |



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